

TOSHIBA CCD Image Sensor CCD (charge coupled device)

TCD2905D

The TCD2905D is a high sensitive and low dark current 5400 elements × 6 line CCD color image sensor which includes CCD drive circuit and clamp circuit. The sensor is designed for scanner.

The device contains a row of 5400 elements × 6 line staggered photodiodes which provide a 48 lines/mm (1200 dpi) across a A4 size paper. The device is operated by 5 V pulse and 12 V power supply.

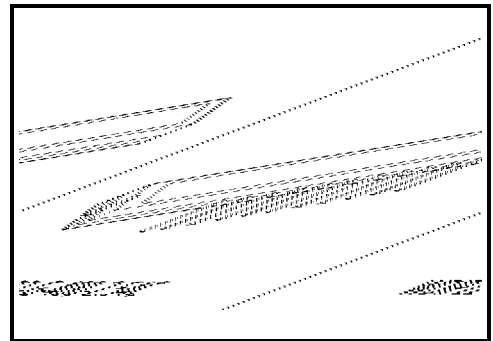
Features

- Number of Image Sensing Elements: 5400 elements × 6 line
- Image Sensing Element Size: 5.25 μm by 5.25 μm on 5.25 μm
- Photo Sensing Region: High sensitive and low dark current PN photodiode
- Distanced Between Photodiode Array: 63 μm (12 lines)
- Clock: 2 phase (5 V)
- Power Supply: 12 V Power Supply Voltage
- Internal Circuit: Clamp Circuit
- Package: 22 pin CERDIP Package
- Color Filter: Red, Green, Blue

Maximum Ratings (Note1)

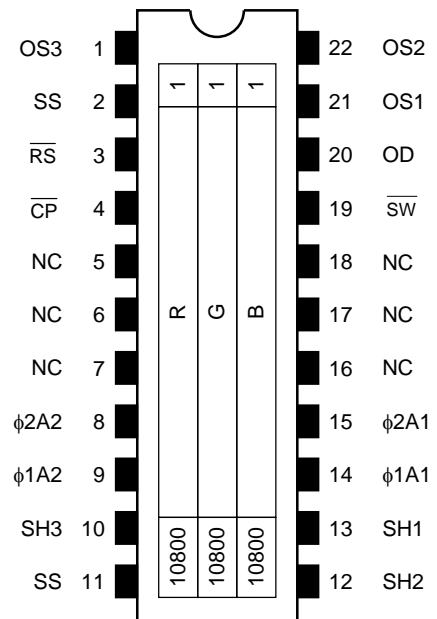
Characteristic	Symbol	Rating	Unit
Clock pulse voltage	$V_{\phi A}$	-0.3~8.0	V
Shift pulse voltage	V_{SH}		
Reset pulse voltage	$V_{\overline{RS}}$		
Clamp pulse voltage	$V_{\overline{CP}}$		
Switch pulse voltage	$V_{\overline{SW}}$		
Power supply voltage	V_{OD}	-0.3~15	V
Operating temperature	T_{opr}	0~60	°C
Storage temperature	T_{stg}	-25~85	°C

Note 1: All voltage are with respect to SS terminals (ground).

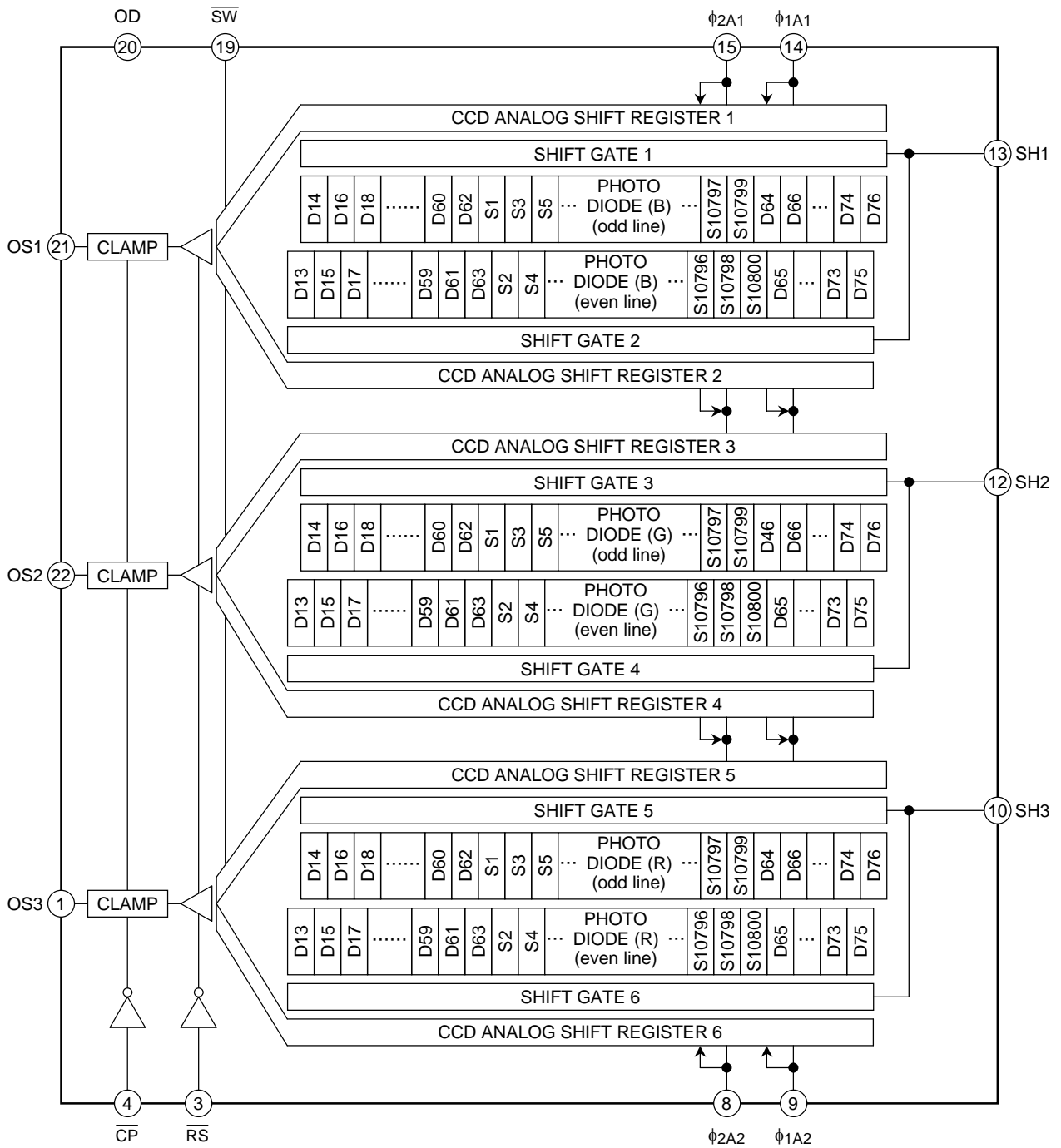


Weight: 4.5 g (typ.)

Pin Connections (top view)



Block Diagram



Pin Names

Pin No.	Symbol	Name	Pin No.	Symbol	Name
1	OS3	Signal Output 3 (red)	12	SH2	Shift Gate 2
2	SS	Ground	13	SH1	Shift Gate 1
3	\overline{RS}	Reset Gate	14	$\phi 1A1$	Clock 1 (phase 1)
4	\overline{CP}	Clamp Gate	15	$\phi 2A1$	Clock 1 (phase 2)
5	NC	Non Connection	16	NC	Non Connection
6	NC	Non Connection	17	NC	Non Connection
7	NC	Non Connection	18	NC	Non Connection
8	$\phi 2A2$	Clock 2 (phase 2)	19	\overline{SW}	Switch Gate
9	$\phi 1A2$	Clock 2 (phase 1)	20	OD	Power
10	SH3	Shift Gate 3	21	OS1	Signal Output 1 (blue)
11	SS	Ground	22	OS2	Signal Output 2 (green)

Optical/Electrical Characteristics

($T_a = 25^\circ\text{C}$, $V_{OD} = 12\text{ V}$, $V_{SW} = 5\text{ V}$, $V_\phi = V_{SH} = V_{\overline{RS}} = V_{\overline{CP}} = 5\text{ V}$ (pulse), $f_\phi = 1\text{ MHz}$, $f_{\overline{RS}} = 2\text{ MHz}$, $t_{INT} = 11\text{ ms}$, light source = a light source + CM500S filter ($t = 1\text{ mm}$), load resistance = 100 k Ω)

Characteristics		Symbol	Min	Typ.	Max	Unit	Note
Sensitivity	Red	R (R)	3.2	4.7	6.2	V/lx·s	(Note2)
	Green	R (G)	4.4	6.4	8.4		
	Blue	R (B)	2.5	3.7	4.9		
Photo response non uniformity		PRNU (1)	—	10	20	%	(Note3)
		PRNU (3)	—	3	12	mV	(Note4)
Register imbalance		RI	—	1	—	%	(Note5)
Saturation output voltage		V_{SAT}	2.0	2.5	—	V	(Note6)
Saturation exposure		SE	0.24	0.39	—	lx·s	(Note7)
Dark signal voltage		V_{DRK}	—	0.5	2.0	mV	(Note8)
Dark signal non uniformity		DSNU	—	2.0	7.0	mV	(Note8)
DC power dissipation		PD	—	480	650	mW	
Total transfer efficiency		TTE	92	98	—	%	
Output impedance		Z_O	—	0.3	1.0	k Ω	
DC output voltage		V_{OS}	5.0	6.0	7.0	V	(Note9)
Reset noise		V_{RSN}	—	0.3	—	V	(Note9)
Random noise		$N_{D\sigma}$	—	0.9	—	mV	(Note10)

Note 2: Sensitivity is defined for each color of signal outputs average when the photosensitive surface is applied with the light of uniform illumination and uniform color temperature.

Note 3: PRNU (1) is defined for each color on a single chip by the expressions below when the photosensitive surface is applied with the light of uniform illumination and uniform color temperature.

$$PRNU (1) = \frac{\Delta X}{\bar{X}} \times 100 (\%)$$

Where \bar{X} is average of total signal output and ΔX is the maximum deviation from \bar{X} . The amount of incident light is shown below.

$$Red = 1/2 \cdot SE$$

$$Green = 1/2 \cdot SE$$

$$Blue = 1/4 \cdot SE$$

Note 4: PRNU (3) is defined as maximum voltage with next pixel, where measured at 5% of SE (typ.)

Note 5: Register imbalance is defined as follows.

$$RI = \frac{\sum_{n=1}^{10799} |x_n - x_{(n+1)}|}{10799 \cdot \bar{X}} * 100 (\%)$$

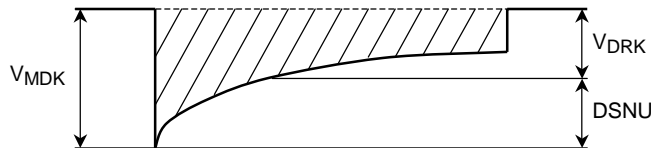
Note 6: V_{SAT} is defined as minimum saturation output of all effective pixels.

Note 7: Definition of SE

$$SE = \frac{V_{SAT}}{R_G} (lx \cdot s)$$

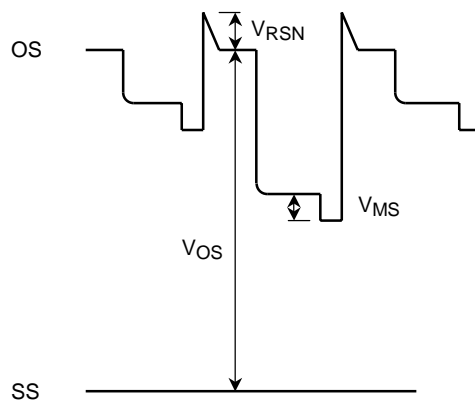
Note 8: V_{DRK} is defined as average dark signal voltage of all effective pixels.

$DSNU$ is defined as different voltage between V_{DRK} and V_{MDK} when V_{MDK} is maximum dark signal voltage.

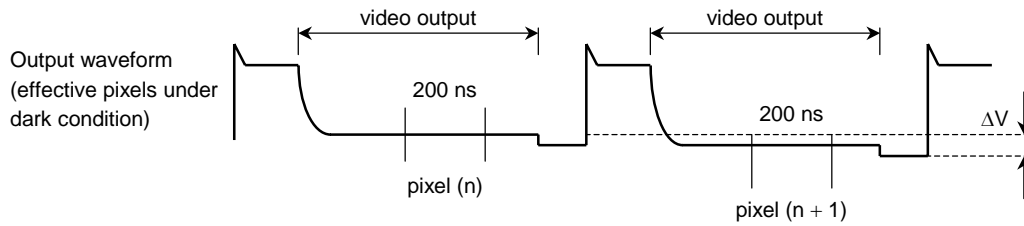


Note 9: DC signal output voltage is defined as follows.

Reset Noise Voltage is defined as follows.



Note 10: Random noise is defined as the standard deviation (sigma) of the output level difference between two adjacent effective pixels under no illumination (i.e. dark conditions) calculated by the following procedure.



- (1) Two adjacent pixels (pixel n and n + 1) after reference level clamp in one reading are fixed as measurement points.
- (2) Each of the output level at video output periods averaged over 200 ns period to get V (n) and V (n + 1).
- (3) V (n + 1) is subtracted from V (n) to get ΔV .

$$\Delta V = V(n) - V(n+1)$$

- (4) The standard deviation of ΔV is calculated after procedure (2) and (3) are repeated 30 times (30 readings).

$$\Delta V = \frac{1}{30} \sum_{i=1}^{30} |\Delta V_i| \quad \sigma = \sqrt{\frac{1}{30} \sum_{i=1}^{30} (\Delta V_i - \overline{\Delta V})^2}$$

- (5) Procedure (2), (3) and (4) are repeated 10 times to get sigma value.
- (6) 10 sigma values are averaged.

$$\bar{\sigma} = \frac{1}{10} \sum_{j=1}^{10} \sigma_j$$

- (7) $\bar{\sigma}$ value calculated using the above procedure is observed $\sqrt{2}$ times larger than that measured relative to the ground level. So we specify random noise as follows.

$$N_{D\sigma} = \frac{1}{\sqrt{2}} \bar{\sigma}$$

Operating Condition

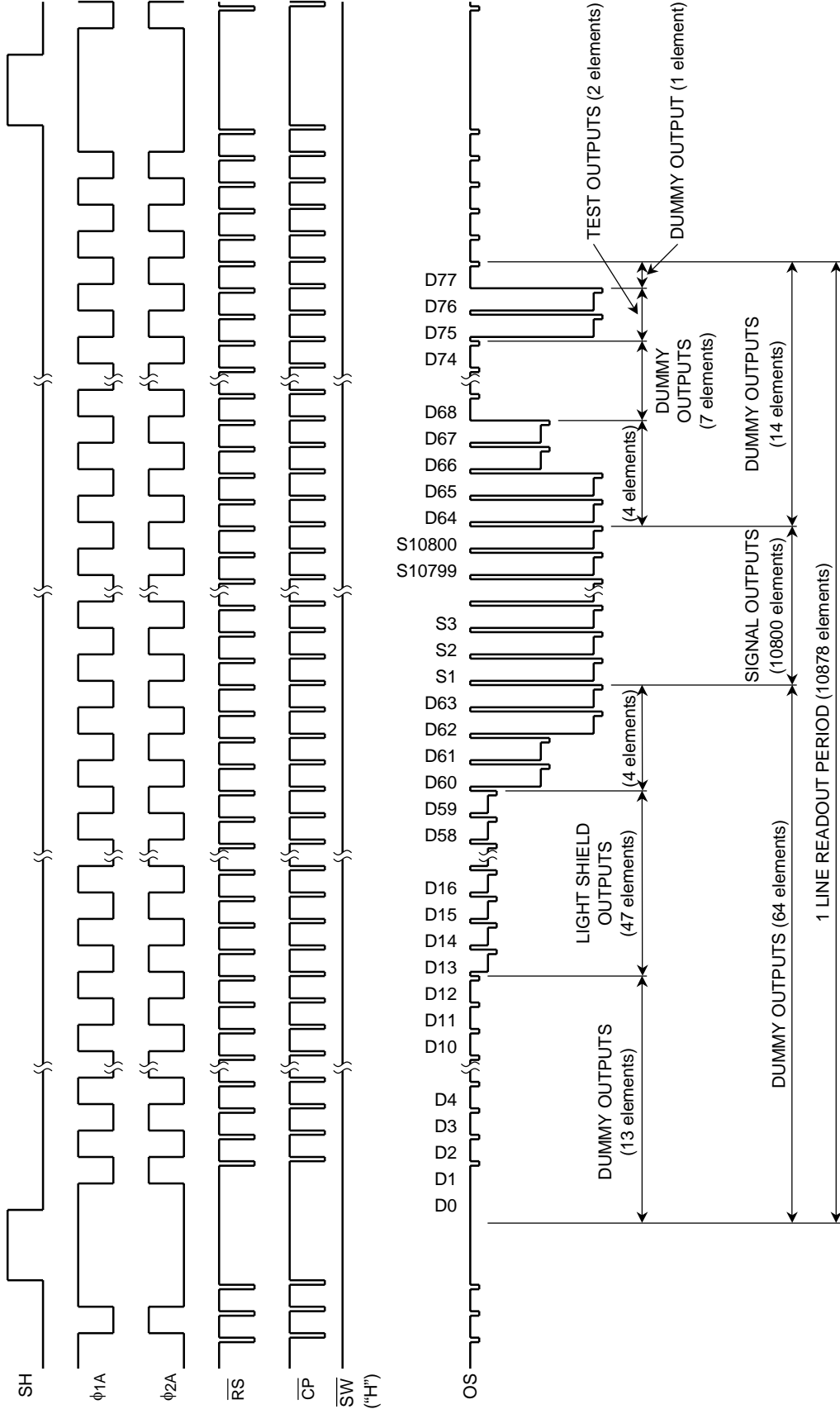
Characteristics		Symbol	Min	Typ.	Max	Unit
Clock pulse voltage	"H" Level	$V_{\phi A}$	4.5	5.0	5.5	V
	"L" Level		0	0	0.3	
Shift pulse voltage	"H" Level	V_{SH}	4.5	5.0	5.5	V
	"L" Level		0	0	0.5	
Reset pulse voltage	"H" Level	$\overline{V_{RS}}$	4.5	5.0	5.5	V
	"L" Level		0	0	0.5	
Clamp pulse voltage	"H" Level	$\overline{V_{CP}}$	4.5	5.0	5.5	V
	"L" Level		0	0	0.5	
Switch pulse voltage	"H" Level	$\overline{V_{SW}}$	4.5	5.0	5.5	V
	"L" Level		0	0	0.5	
Power supply voltage		V_{OD}	11.4	12.0	13.0	V

Clock Characteristics (Ta = 25°C)

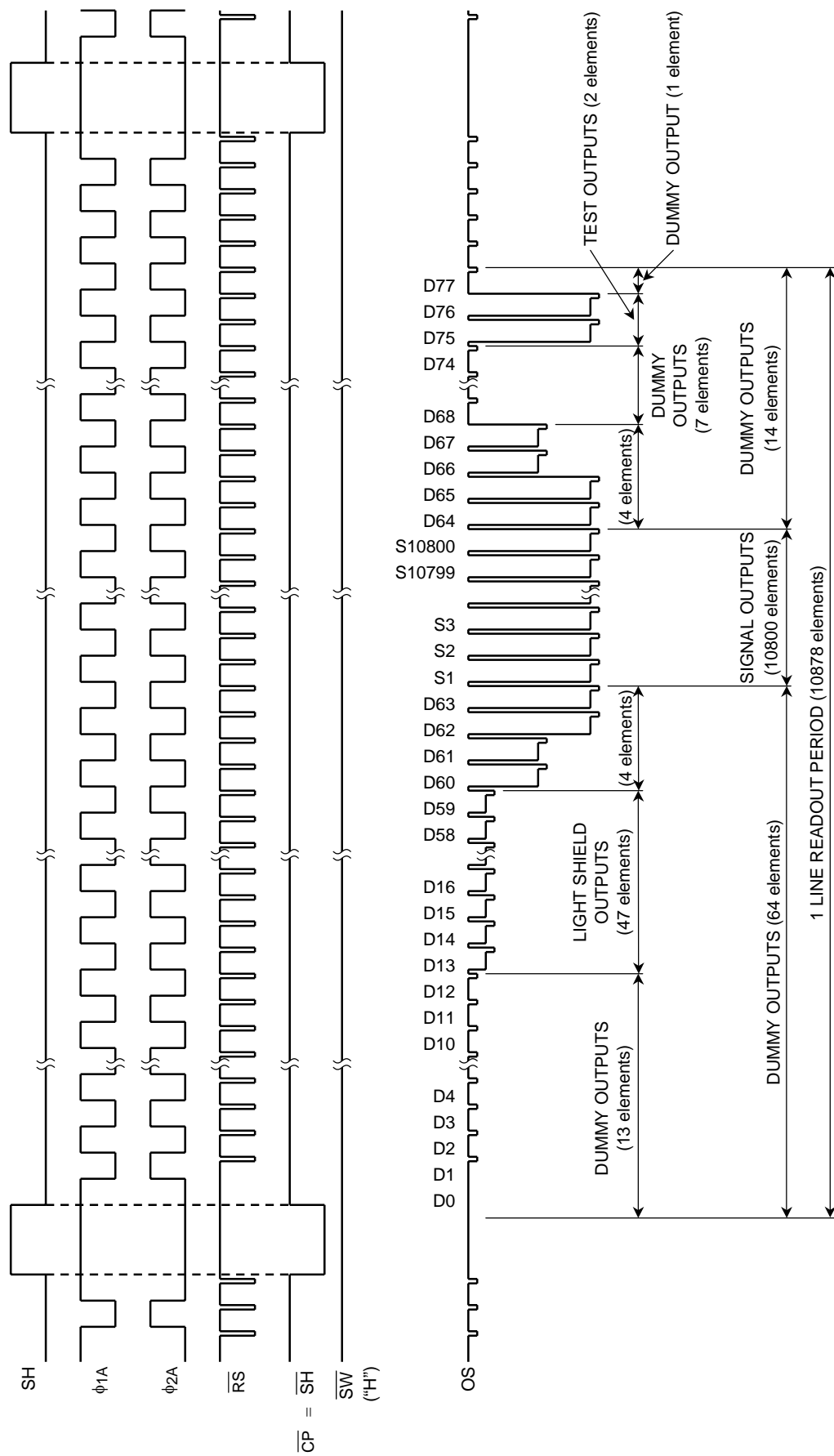
Characteristics		Symbol	Min	Typ.	Max	Unit
Clock pulse frequency		$f_{\phi A}$	0.15	1.0	5.0	MHz
Reset pulse frequency		$f_{\overline{RS}}$	0.3	2.0	10.0	MHz
Clamp pulse frequency		$f_{\overline{CP}}$	0.3	2.0	10.0	MHz
Clock capacitance (Note 11)		$C_{\phi A}$	—	400	—	pF
Shift gate capacitance		C_{SH}	—	50	—	pF
Reset gate capacitance		$C_{\overline{RS}}$	—	10	—	pF
Clamp gate capacitance		$C_{\overline{CP}}$	—	10	—	pF
Switch gate capacitance		$C_{\overline{SW}}$	—	10	—	pF

Note 11: $V_{OD} = 12\text{ V}$

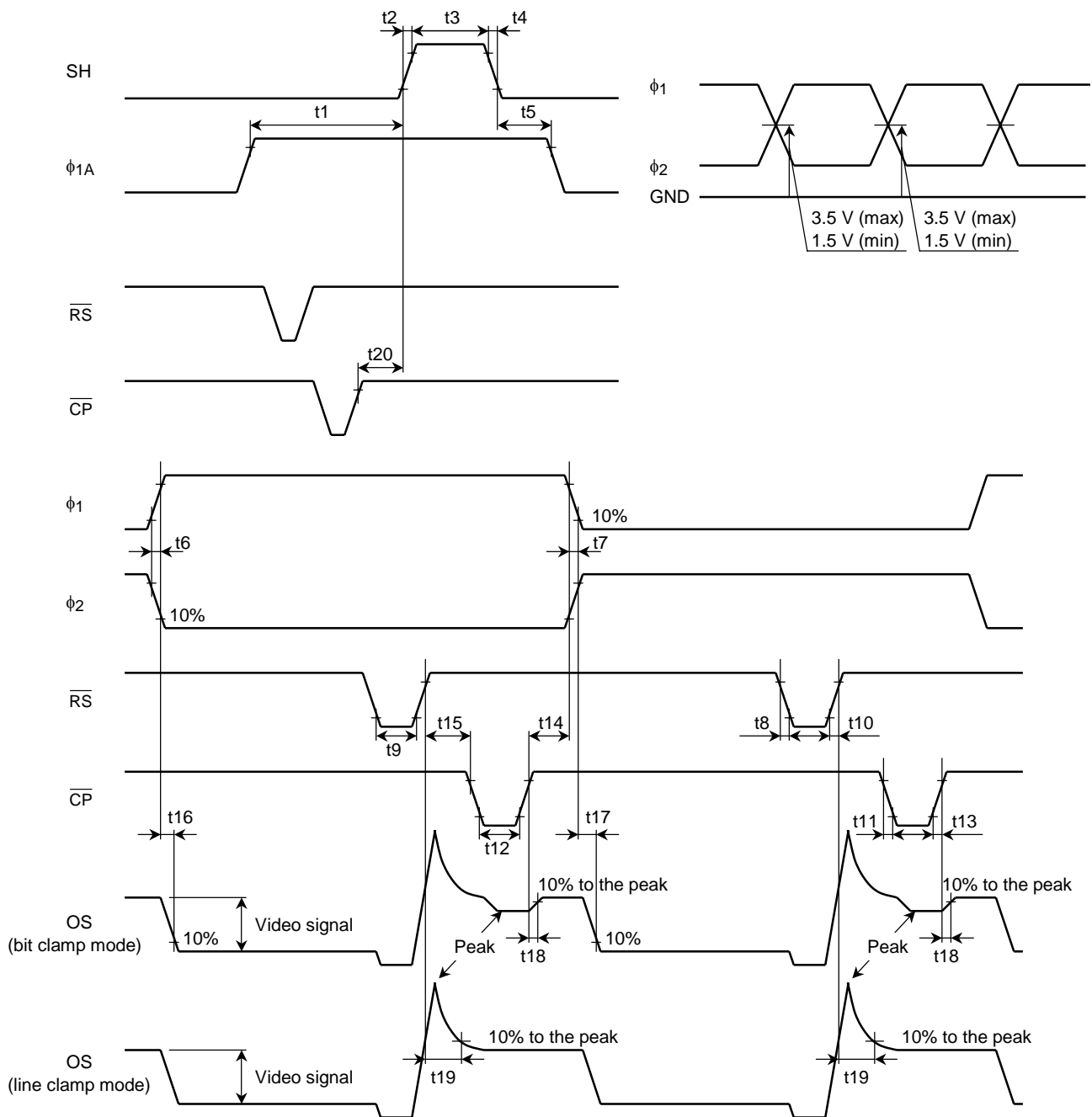
Timing Chart (bit clamp mode)



Timing Chart (line clamp mode)



Timing Requirements

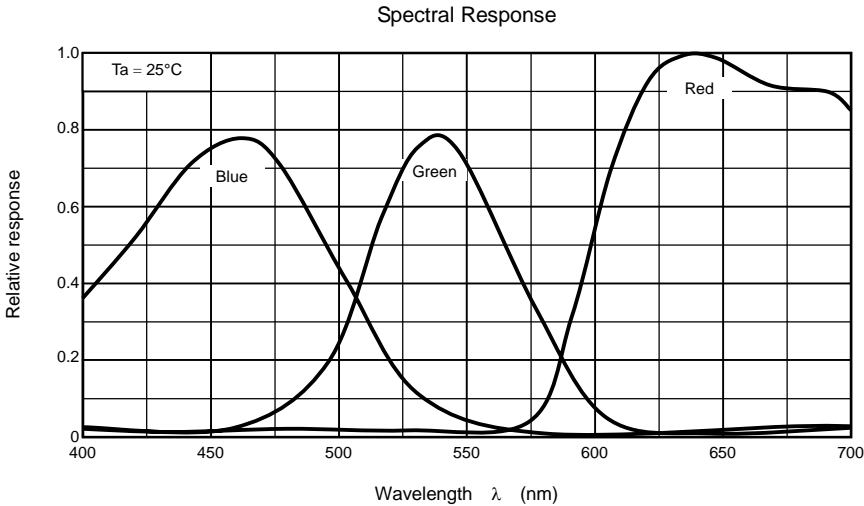


Characteristics	Symbol	Min	Typ. (Note 12)	Max	Unit
Pulse timing of SH and ϕ_1	t1	110	1000	—	ns
	t5	800	1000	—	
SH pulse rise time, fall time	t2, t4	0	50	—	ns
SH pulse width	t3	3000	5000	—	ns
ϕ_1, ϕ_2 pulse rise time, fall time	t6, t7	0	50	—	ns
\overline{RS} pulse rise time, fall time	t8, t10	0	20	—	ns
\overline{RS} pulse width	t9	15	100	—	ns
\overline{CP} pulse rise time, fall time	t11, t13	0	20	—	ns
\overline{CP} pulse width	t12	25	100	—	ns
Pulse timing of ϕ_{1A}, ϕ_{2A} and \overline{CP}	t14	10	40	—	ns
Pulse timing of \overline{RS} and \overline{CP}	t15	0	100	—	ns
Video data delay time (Note 13)	t16, t17	—	20	—	ns
Reference level settle time	t18	—	20	—	ns
	t19	—	35	—	ns
Pulse timing of SH and \overline{CP}	t20	0	500	—	ns

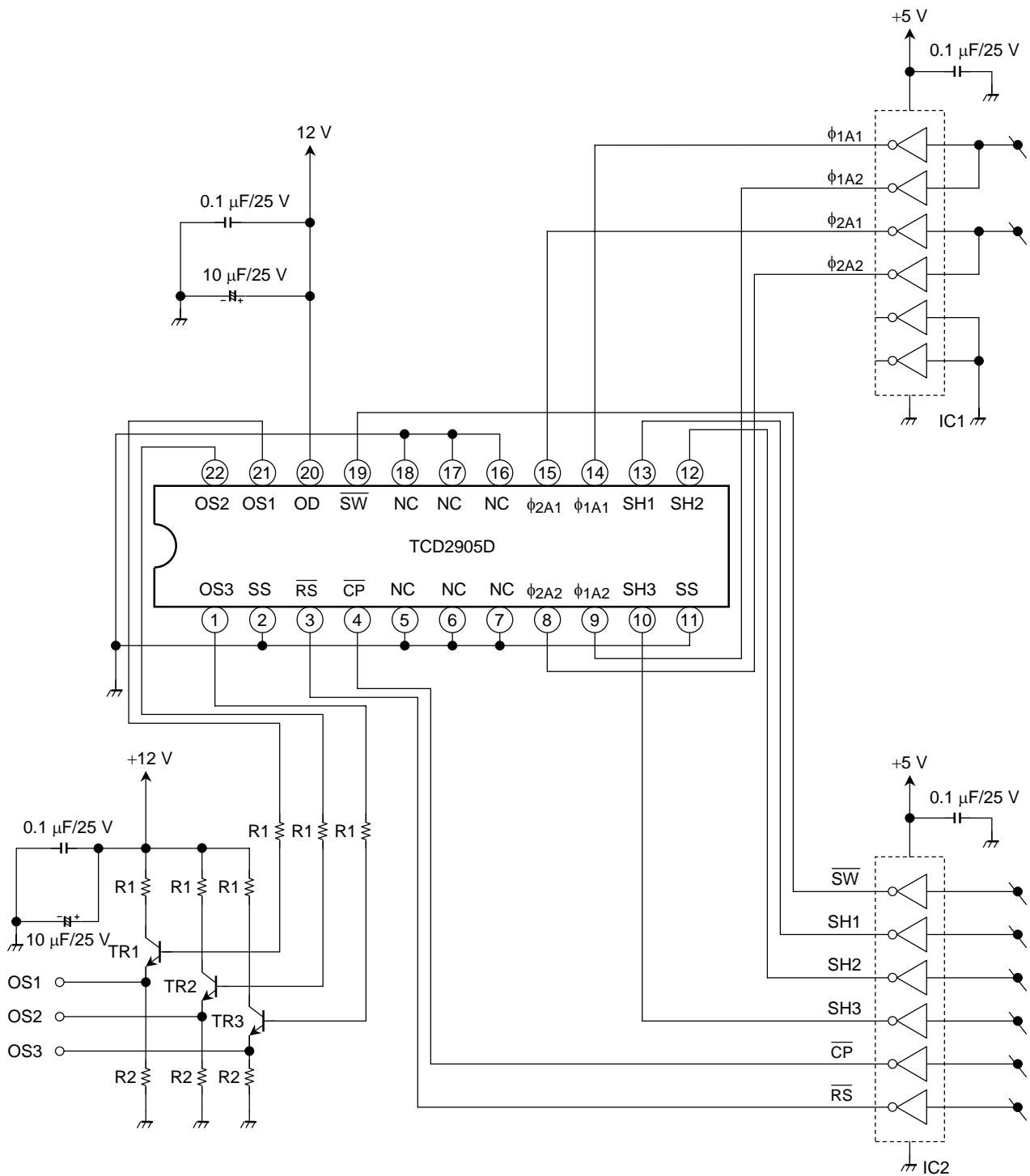
Note 12: Typ. is the case of $f_\phi = 1.0$ MHz.

Note 13: Load resistance is 100 k Ω .

Typical Spectral Response



Typical Drive Circuit



IC1, 2: TC74HC04AP
 TR1, 2, 3: 2SC1815-Y
 R1: 150 Ω
 R2: 1500 Ω

Caution**1. Window Glass**

The dust and stain on the glass window of the package degrade optical performance of CCD sensor. Keep the glass window clean by saturating a cotton swab in alcohol and lightly wiping the surface, and allow the glass to dry, by blowing with filtered dry N₂. Care should be taken to avoid mechanical or thermal shock because the glass window is easily to damage.

2. Electrostatic Breakdown

Store in shorting clip or in conductive foam to avoid electrostatic breakdown. CCD Image Sensor is protected against static electricity, but inferior puncture mode device due to static electricity is sometimes detected. In handling the device, it is necessary to execute the following static electricity preventive measures, in order to prevent the trouble rate increase of the manufacturing system due to static electricity.

- a. **Prevent the generation of static electricity due to friction by making the work with bare hands or by putting on cotton gloves and non-charging working clothes.**
- b. **Discharge the static electricity by providing earth plate or earth wire on the floor, door or stand of the work room.**
- c. **Ground the tools such as soldering iron, radio cutting pliers or of pincer. It is not necessarily required to execute all precaution items for static electricity. It is all right to mitigate the precautions by confirming that the trouble rate within the prescribed range.**

3. Incident Light

CCD sensor is sensitive to infrared light. Note that infrared light component degrades resolution and PRNU of CCD sensor.

4. Lead Frame Forming

Since this package is not strong against mechanical stress, you should not reform the lead frame. We recommend to use a IC-inserter when you assemble to PCB.

5. Soldering

Soldering by the solder flow method cannot be guaranteed because this method may have deleterious effects on prevention of window glass soiling and heat resistance.

Using a soldering iron, complete soldering within ten seconds for lead temperatures of up to 260°C, or within three seconds for lead temperatures of up to 350°C.

Application Note

The TCD2905D can be operated in two modes: Normal Readout Mode and Even Line Readout Mode. Each mode is selected by \overline{SW} terminal.

\overline{SW}	Mode	Application Example
H	Normal Readout Mode	1200 DPI/A4 Reading
L	Even Line Readout Mode	600 DPI/A4 Reading

Normal Readout Mode

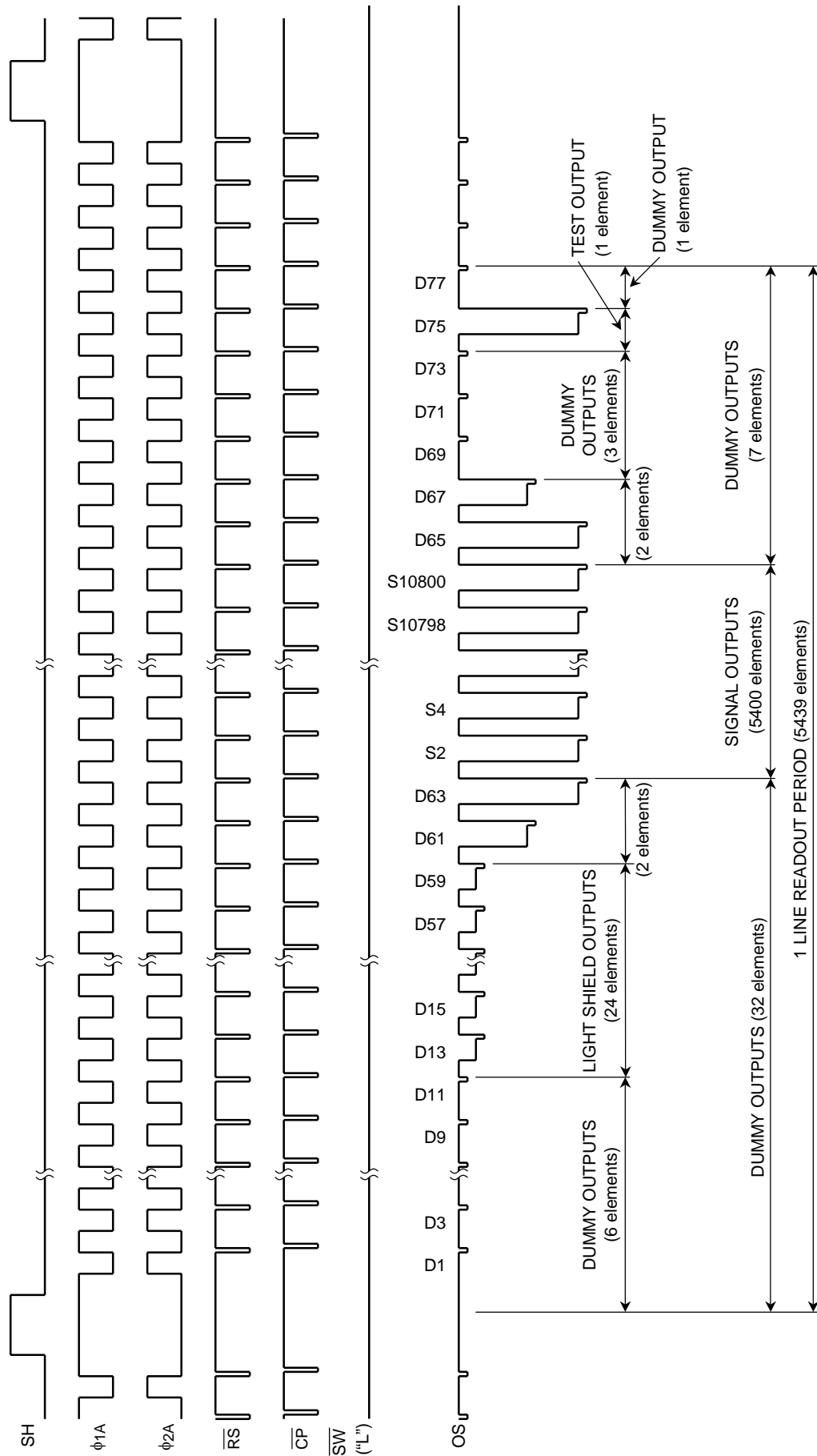
In Normal Readout Mode, the dummy and signal outputs in odd and even lines are read out. This mode provides 1200 DPI/A4 resolution. The timing for this mode is shown in page 8/21, 9/21 and 10/21.

Even Line Readout Mode

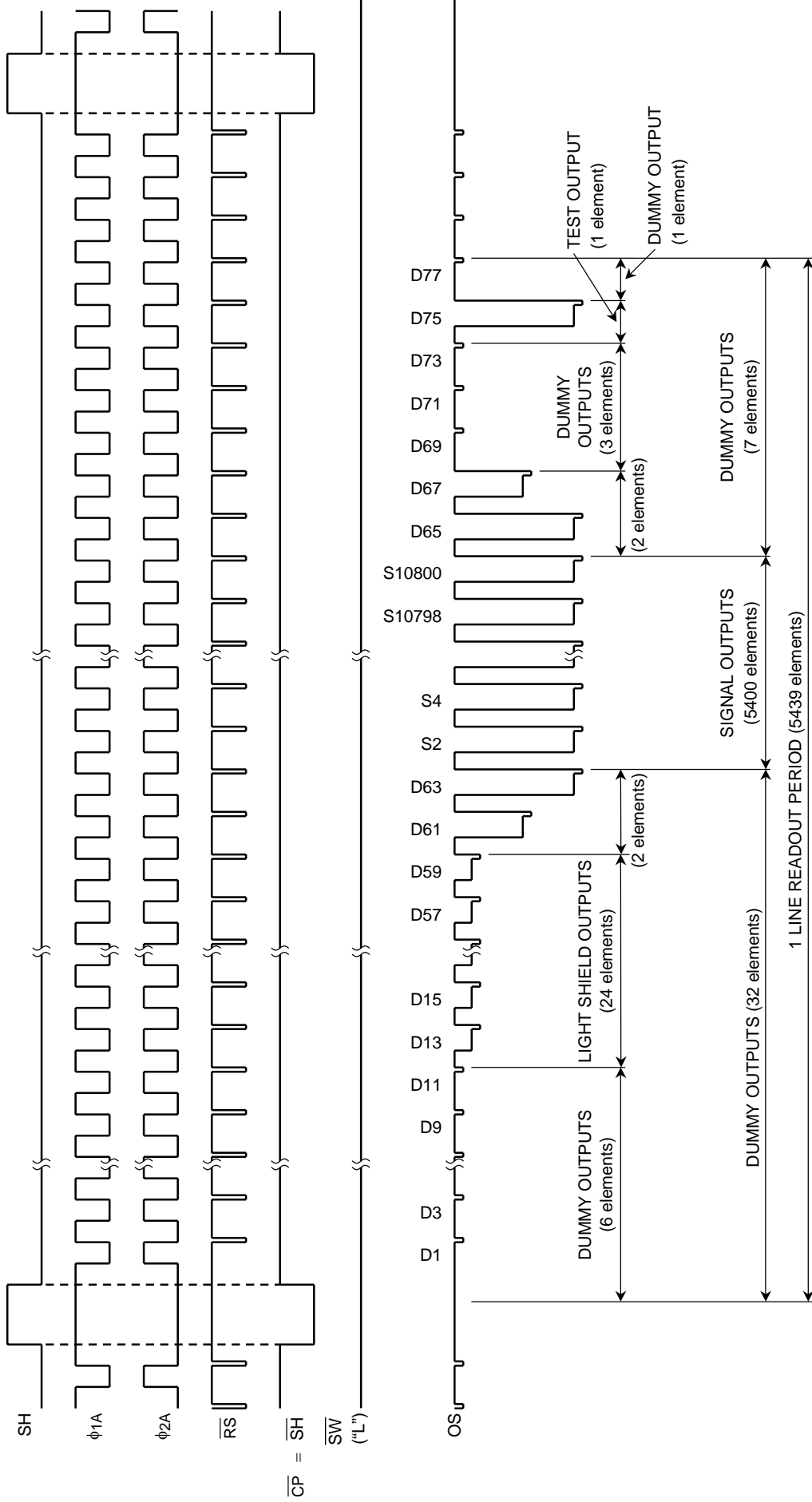
In Even Line Readout Mode, the dummy and signal outputs in even lines are read out. The dummy and signal outputs in odd lines cannot be read out in this mode. This mode provides 600 DPI/A4 resolution. Timing examples for 600 DPI/A4 reading using this mode are shown in page 15/21, 16/21 and 19/21 for reference.

In this mode, signal charges of adjacent pixels in even line can be merged at an output stage capacitor using intermittent reset drive. Timing examples for 300 DPI/A4 reading using this mode are shown in page 17/21, 18/21 and 20/21 for reference.

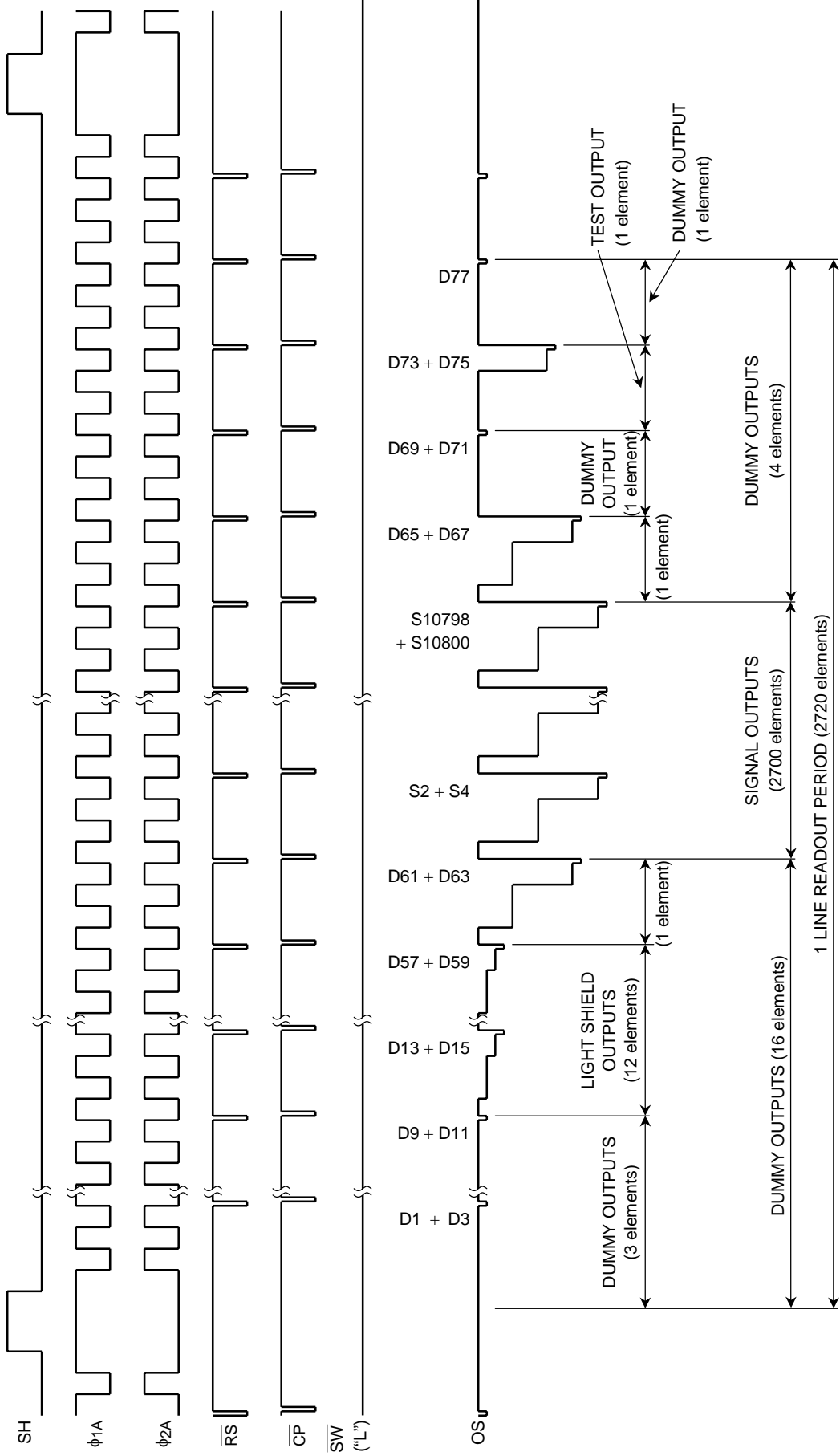
Timing Chart (600 dpi mode)



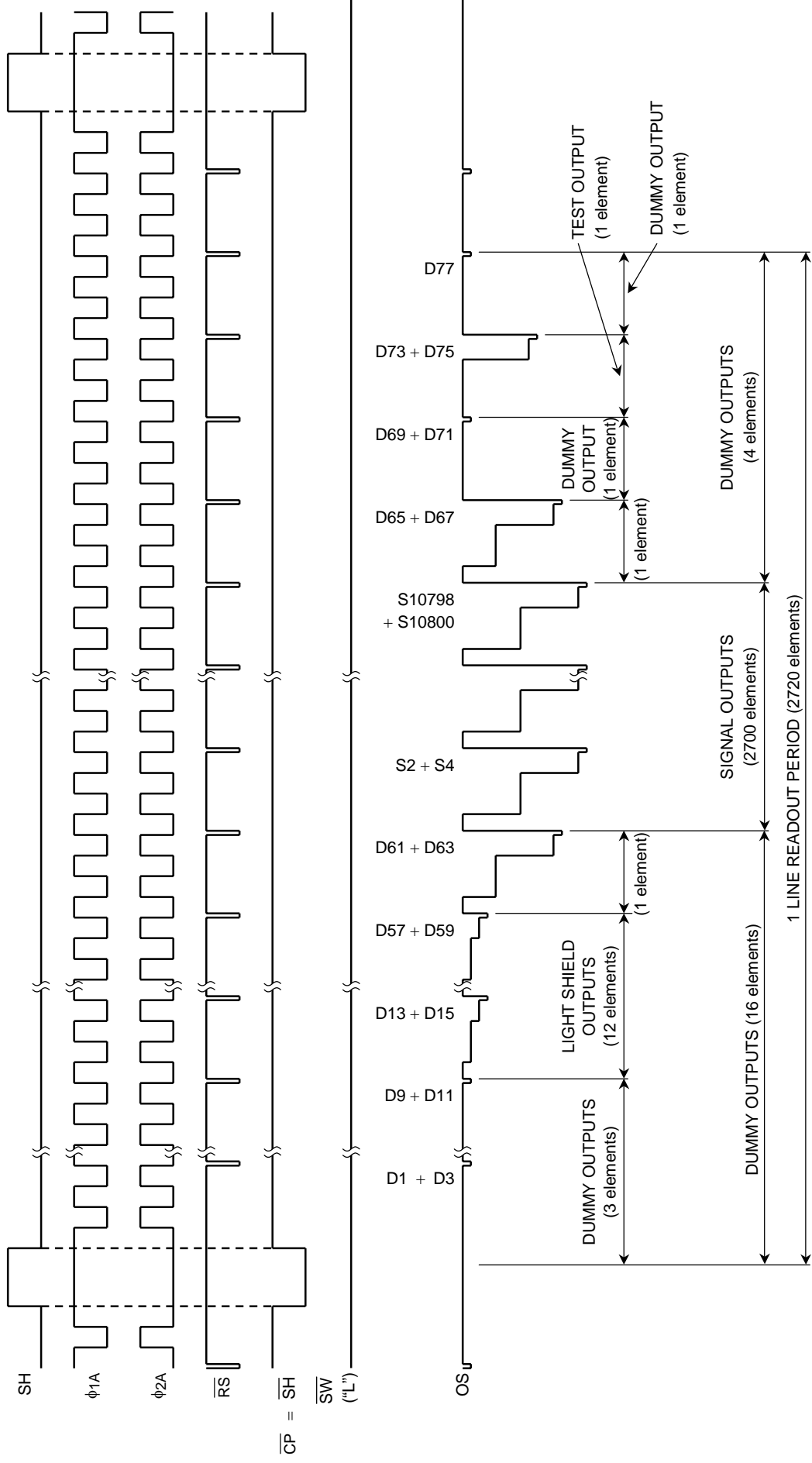
Timing Chart (600 dpi/line clamp mode)



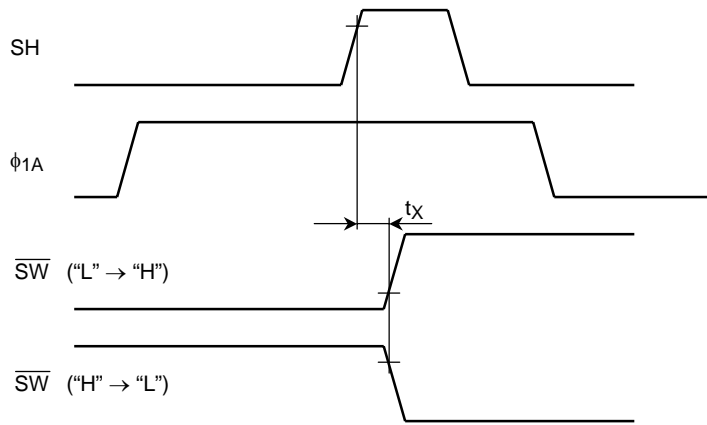
Timing Chart (300 dpi mode)



Timing Chart (300 dpi/line clamp mode)

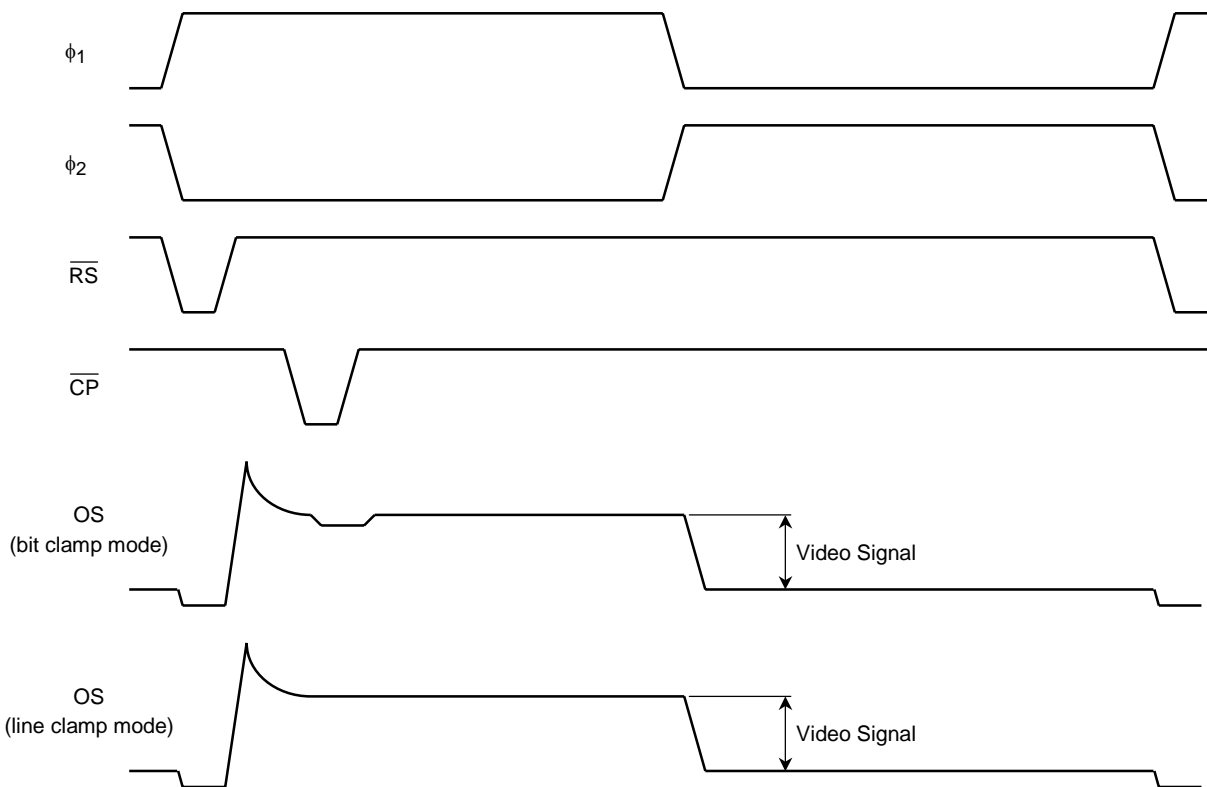


Timing Example

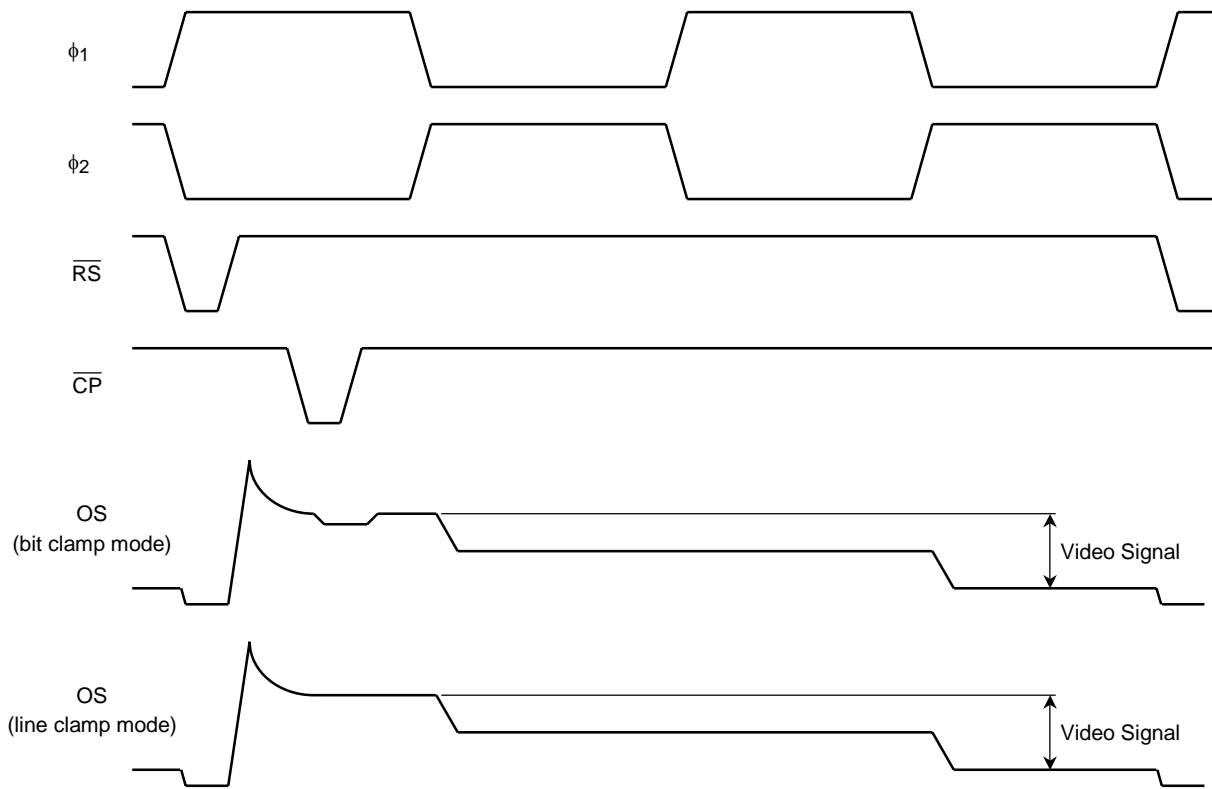


Characteristic	Symbol	Min	Typ.	Max	Unit
Pulse timing of SH and \overline{SW}	t_x	0	0	—	ns

Timing Example (600 dpi mode: \overline{SW} = "L")



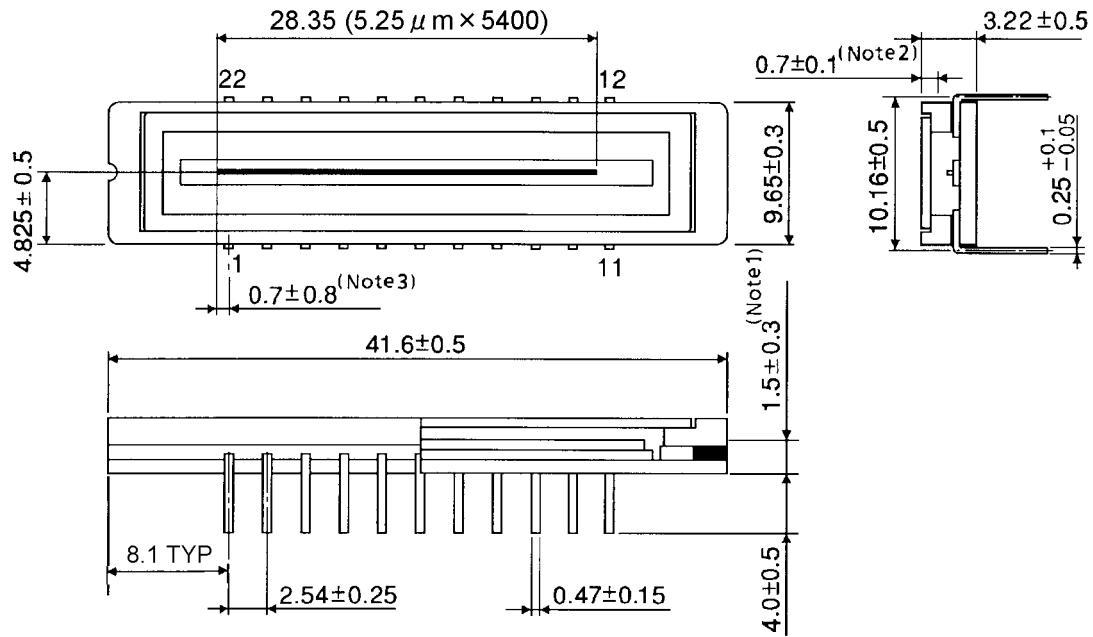
Timing Example (300 dpi mode: \overline{SW} = "L")



Package Dimensions

WDIP22-G-400-2.54C(B)

Unit : mm



(Note 1) : TOP OF CHIP TO BOTTOM OF PACKAGE.

(Note 2) : GLASS THICKNESS (n = 1.5)

(Note 3) : No.1 SENSOR ELEMENT (S1) TO CENTER OF No.1 PIN.

Weight: 4.5 g (typ.)

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